

GI42C

PNP EPITAXIAL PLANAR TRANSISTOR

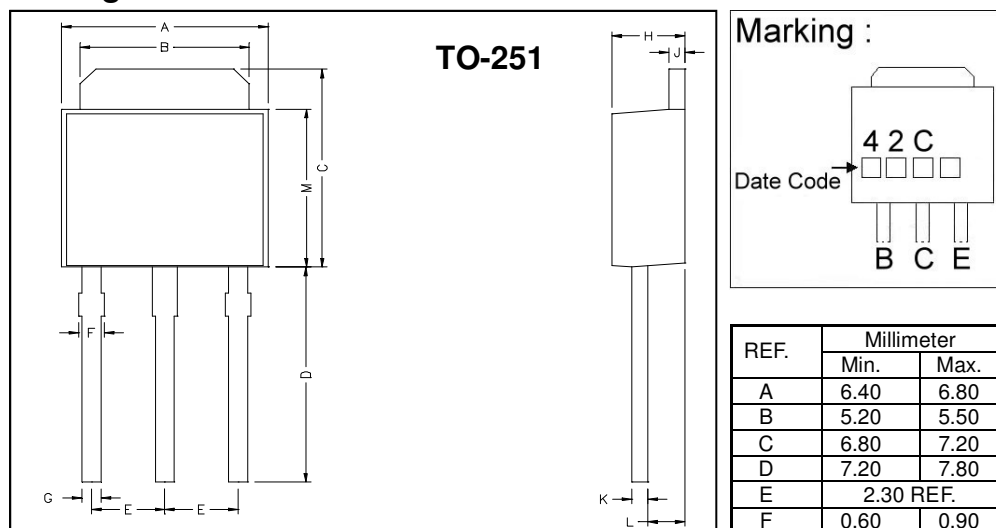
Description

The GI42C is designed for use in general purpose amplifier and switching applications.

Features

*Complementary to GI41C

Package Dimensions



Absolute Maximum Ratings (Ta = 25°C, unless otherwise specified)

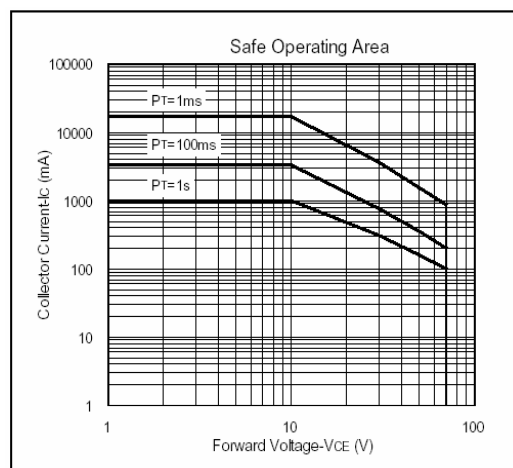
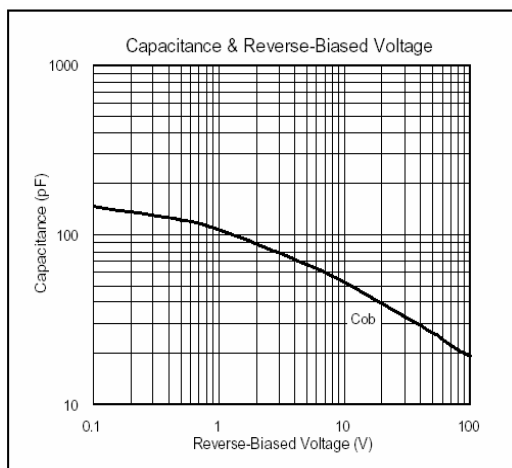
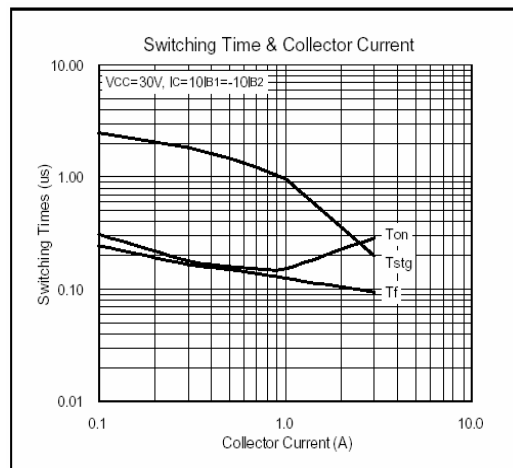
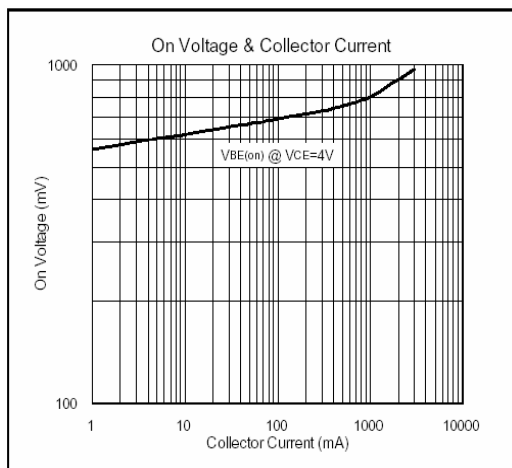
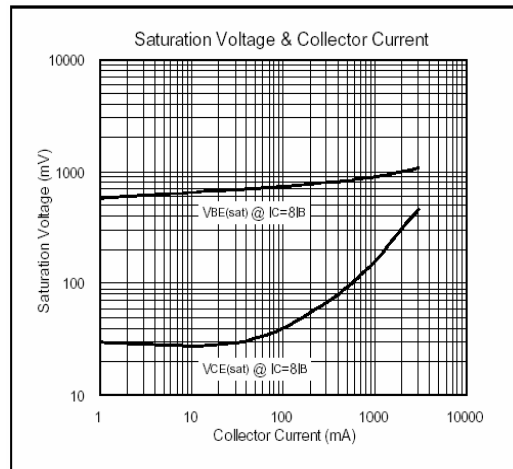
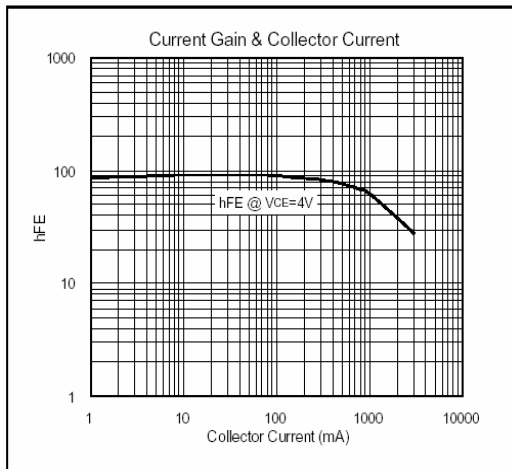
Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	VCBO	-100	V
Collector to Emitter Voltage	VCEO	-100	V
Emitter to Base Voltage	VEBO	-5	V
Collector Current (DC)	IC	-6	A
Collector Current (Pulse)	IC	-10	A
Junction Temperature	Tj	+150	°C
Storage Temperature	TSTG	-55 ~ +150	°C
Total Power Dissipation	PD	2	W
	PD(Tc=25°C)	20	W

Electrical Characteristics (Rating at Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-100	-	-	V	IC=-1mA, IE=0
*BVCEO	-100	-	-	V	IC=-30mA, IB=0
BVEBO	-5	-	-	V	IE=-100uA, IC=0
ICES	-	-	-10	uA	VCE=-100V, VEB=0V
ICEO	-	-	-50	uA	VCE=-60V, IB=0
IEBO	-	-	-500	uA	VEB=-5V, IC=0
*VCE(sat)	-	-	-1.5	V	IC =-6A, IB=-600mA
*VBE(on)	-	-	-2.0	V	VCE=-4V, IC=-6A
*hFE1	30	-	-		VCE=-4V, IC=-300mA
*hFE2	15	-	75		VCE=-4V, IC=-3A
fT	3	-	-	MHz	VCE=-10V, IC=-500mA, f=1MHz

* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Characteristics Curve



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